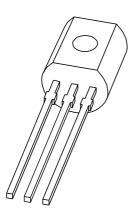
DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS4350S 50 V low V_{CEsat} NPN transistor

Product specification

2001 Nov 19





50 V low V_{CEsat} NPN transistor

PBSS4350S

FEATURES

- High power dissipation (830 mW)
- · Ultra low collector-emitter saturation voltage
- 3 A continuous current
- · High current switching
- Improved device reliability due to reduced heat generation

APPLICATIONS

- · Medium power switching and muting
- · Linear regulators
- DC/DC convertor
- · Supply line switching circuits
- · Battery management applications
- · Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT54 plastic package. PNP complement: PBSS5350S.

MARKING

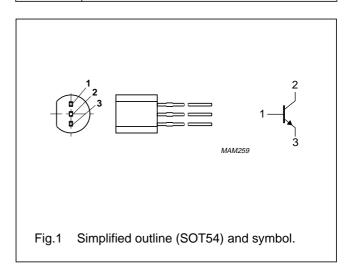
TYPE NUMBER	MARKING CODE
PBSS4350S	S4350S

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	50	V
I _C	collector current (DC)	3	Α
I _{CM}	peak collector current		Α
R _{CEsat}	equivalent on-resistance	<145	mΩ

PINNING

PIN	DESCRIPTION			
1	base			
2	collector			
3	emitter			



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V _{CEO}	collector-emitter voltage	open base	_	50	V
V _{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current (DC)		_	3	Α
I _{CM}	peak collector current		_	5	А
I _{BM}	peak base current		_	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	830	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

50 V low V_{CEsat} NPN transistor

PBSS4350S

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; note 1	150	K/W
_	ambient			

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

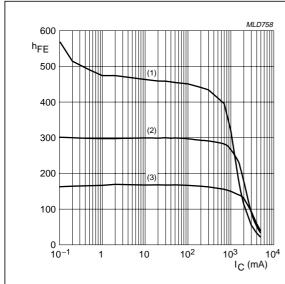
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	_	_	100	nA
		V _{CB} = 50 V; I _E = 0; T _j = 150 °C	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 500 mA	200	_	_	
		V _{CE} = 2 V; I _C = 1 A; note 1	200	_	_	
		V _{CE} = 2 V; I _C = 2 A; note 1	100	_	_	
V _{CEsat}	collector-emitter saturation	I _C = 500 mA; I _B = 50 mA	_	_	90	mV
	voltage	I _C = 1 A; I _B = 50 mA	_	_	170	mV
		I _C = 2 A; I _B = 200 mA; note 1	_	_	290	mV
R _{CEsat}	equivalent on-resistance	I _C = 2 A; I _B = 200 mA; note 1	_	110	<145	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 2 A; I _B = 200 mA; note 1	_	_	1.2	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 1 A; note 1	_	_	1.1	V
f _T	transition frequency	I _C = 100 mA; V _{CE} = 5 V; f = 100 MHz	100	_	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	_	30	pF

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

50 V low V_{CEsat} NPN transistor

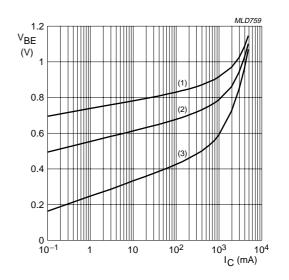
PBSS4350S



 $V_{CE} = 2 V$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55$ °C.

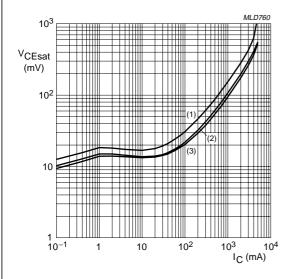
Fig.2 DC current gain as a function of collector current; typical values.



V_{CE} = 2 V.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

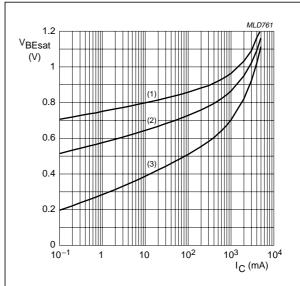
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B}=20.$

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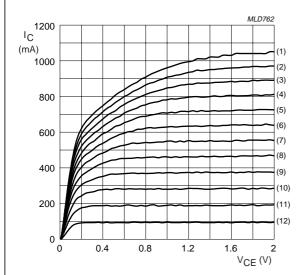
- (1) $T_{amb} = -55 \, ^{\circ}C.$
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

2001 Nov 19

50 V low V_{CEsat} NPN transistor

PBSS4350S



 $T_{amb} = 25 \, ^{\circ}C.$

(1) $I_B = 3.96 \text{ nA}.$

(5) $I_B = 2.64 \text{ nA}.$

(9) $I_B = 1.32 \text{ nA}.$

(2) $I_B = 3.63 \text{ nA}.$

(6) $I_B = 2.31 \text{ nA}.$

(10) $I_B = 0.99 \text{ nA}$.

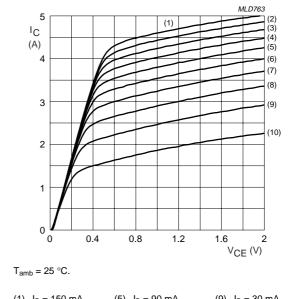
(3) $I_B = 3.30 \text{ nA}.$

(7) $I_B = 1.98 \text{ nA}.$ (8) $I_B = 1.65 \text{ nA}.$ (11) $I_B = 0.66 \text{ nA}$.

(4) $I_B = 2.97 \text{ nA}.$

(12) $I_B = 0.33 \text{ nA}$.

Fig.6 Collector current as a function of collector-emitter voltage; typical values.



(1) $I_B = 150 \text{ mA}$.

(5) $I_B = 90 \text{ mA}.$

(9) $I_B = 30 \text{ mA}.$

(2) $I_B = 135 \text{ mA}.$

(6) $I_B = 75 \text{ mA}.$

(10) $I_B = 15 \text{ mA}$.

(3) $I_B = 120 \text{ mA}.$ (4) $I_B = 105 \text{ mA}.$ (7) $I_B = 60 \text{ mA}.$ (8) $I_B = 45 \text{ mA}.$

Collector current as a function of collector-emitter voltage; typical values.

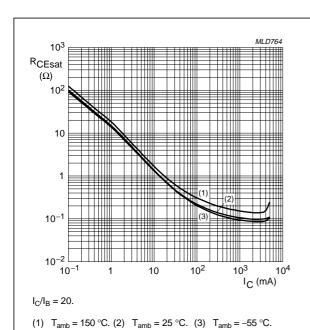


Fig.8 Collector-emitter equivalent on-resistance as a function of collector current; typical values.

2001 Nov 19 5

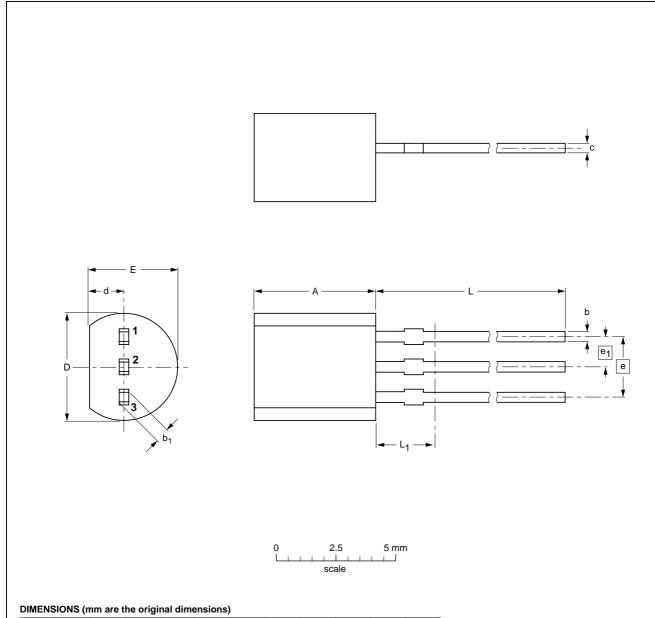
50 V low V_{CEsat} NPN transistor

PBSS4350S

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFERENCES EUROPEAN ISSUE D							EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE				
SOT54		TO-92	SC-43		$ \ \ \bigoplus \big($	97-02-28				

50 V low V_{CEsat} NPN transistor

PBSS4350S

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